RELEASE A DATA SHEET





# **GRF2140**

# Low Current LNA with Bypass 0.085 to 4.2 GHz

#### **FEATURES**

- Flexible Bias Voltage
- Optimal for Low IDDQ to 8 mA
- ullet Simple Matching to 50  $\Omega$
- Process: GaAs pHEMT
- Compact 1.5 x 1.5 mm DFN-6 Package

Reference: 3.3 V / 18 mA / 1.95 GHz

#### **Gain Mode**

Gain: 17.8 dBOP1dB: 9.3 dBmOIP3: 20 dBm

• Evaluation Board Noise Figure: 1.1 dB

#### **Bypass Mode**

• Gain: -2.5 dB

OP1dB: 21.8 dBm

• OIP3: 39 dBm

#### **APPLICATIONS**

- WiFi Access Points
- Mobile WiFi Devices
- Cellular Boosters
- Drones
- UHF/900/2400 ISM

#### **DESCRIPTION**

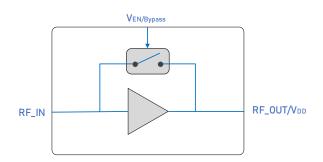
The GRF2140 is a low noise amplifier (LNA) with bypass designed for high-performance WLAN/ISM and other applications up to 4.2 GHz.

The device can be operated from a single supply voltage of 2.7 to 5 volts with a typical bias condition of 3.3 volts and 18 mA.

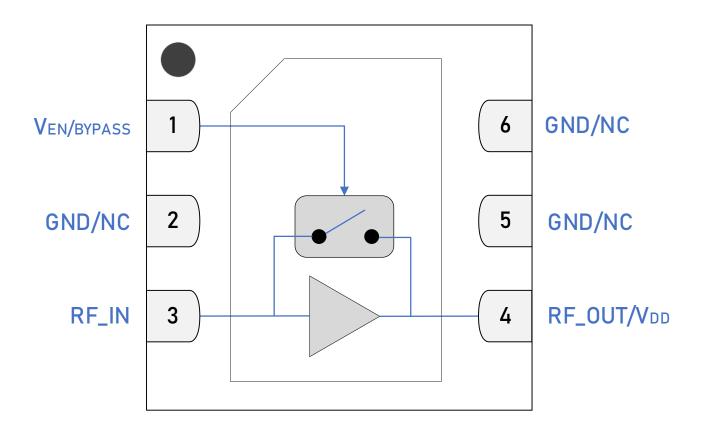
Please consult with the GRF applications engineering team for custom tuning/evaluation board data and device S-parameters.

Additional tunes can be found on the GRF2140 "Custom Tunes" product page: GRF2140 Custom Tunes

#### **B BLOCK DIAGRAM**







1.5 x 1.5 mm DFN-6 Pin Out (Top View)



RELEASE A DATA SHEET

# **Pin Assignments**

Pin	Name	Description	Note
1	VENABLE/BYPASS	V <sub>EN/BYPASS</sub> Control	$V_{\text{EN/BYPASS}}$ and series resistor set $I_{\text{DDQ}}$ . $V_{\text{EN/BYPASS}} < 0.3$ volts disables device. On-die pulldown resistor will turn the device off if this node is allowed to float.
2, 5, 6	GND/NC	Ground or No Connect	No internal connection to die. It is recommended these pins be connected to ground.
3	RF_IN	RF Input	Requires external DC block.
4	RF_OUT/V <sub>DD</sub>	RF Output	Requires external bias inductor followed by DC block.
PKG BASE	GND	Ground	Provides DC and RF ground for device, as well as thermal heat sink. Recommend multiple 8 mil vias beneath the package for optimal RF and thermal performance. Refer to evaluation board top layer graphic on schematic page.

# **Control Logic Truth Table**

Mode	Description	VEN/BYPASS
High Gain	High Gain	1
Bypass	Bypass Mode	0
Logic Level "0"	Logic Low	0 V to 0.3 V
Logic Level "1"	Logic High	1.5 V to VDD



**Absolute Ratings** 

Parameter	Symbol	Min.	Max.	Unit
Supply Voltage	V <sub>DD</sub>	0	6	V
RF Input Power: Load VSWR < 2:1, V <sub>DD</sub> = 5 V, V <sub>EN/BYPASS</sub> = 5 V (Gain Mode)	P <sub>IN MAX</sub>		15	dBm
Operating Temperature (package base)	TPKG BASE	-40	105	°C
Maximum Channel Temperature (MTTF > 10 <sup>6</sup> hours)	T <sub>MAX</sub>		170	°C
Maximum Dissipated Power	Pdiss max		200	mW

#### **Electrostatic Discharge**

Human Body Model	НВМ	100		V	
------------------	-----	-----	--	---	--

#### Storage

Storage Temperature	Тѕтс	-65	150	°C
Moisture Sensitivity Level	MSL		1	



#### **Caution! ESD Sensitive Device.**

#### Exceeding Absolute Maximum Rating conditions may cause permanent damage.

Note: For additional information, please refer to Package Manufacturing Information | Guerrilla RF (guerrilla-rf.com)



All Guerrilla RF products are provided in RoHS compliant lead (Pb)-free packaging requiring no exemptions. Additional information for this topic can be found at this link - *Environmental and Restricted Substance Statement Library* 



# **GRF2140** Low Current LNA with Bypass 0.085 to 4.2 GHz

# **Recommended Operating Conditions**

		S	Specification				
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
Supply Voltage	V <sub>DD</sub>	2.7	3.3	5	V		
Operating Temperature (package base)	T <sub>PKG</sub> BASE	-40		105	°C		
RF Frequency Range	F <sub>RF</sub>	0.085	1.95	4.2	GHz	Typical application schematic with external matching components (notes 1 & 2).	
RF_IN Port Impedance	Z <sub>RFIN</sub>		50		Ω	Single-ended.	
RF_OUT Port Impedance	Zrfout		50		Ω	Single-ended.	

**Note 1:** Operation outside of this range is supported by using different custom tunes. Examples of other optimized tunes can be found here: <u>GRF2140</u> <u>Custom Tunes</u>

Note 2: Contact the Guerrilla RF Applications team for guidance on optimizing the tuning of the device for alternative bands.



# **Nominal Operating Parameters – General**

The following conditions apply unless noted otherwise: typical application schematic using the 1.7 to 2.2 GHz tuning set.  $V_{DD} = 3.3 \text{ V}$ ,  $V_{EN/BYPASS} = 3.3 \text{ V}$ ,  $I_{DDQ} = 18 \text{ mA}$ . M5 = 500  $\Omega$ ,  $F_{TEST} = 1.95 \text{ GHz}$ ,  $T_{PKGBASE} = 25 ^{\circ}\text{C}$ . Evaluation board losses are included within the specifications.

		Specification		Specification		Specification		Specification		pecification		Specification		
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition								
Supply Current	I <sub>DDQ</sub>	13	18	25	mA	V <sub>DD</sub> = 3.3 V, V <sub>EN/BYPASS</sub> = 3.3 V.								
Enable Current	IENABLE		1	3	mA	V <sub>DD</sub> = 3.3 V, V <sub>EN/BYPASS</sub> = 3.3 V.								
Switching Rise Time	T <sub>RISE</sub>		100		ns	Bypass mode to Gain mode (note 3).								
Switching Fall Time	T <sub>FALL</sub>		50		ns	Gain mode to Bypass mode (note 4).								

#### **Disabled Mode**

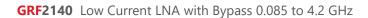
Leakage Current I <sub>LE</sub>	leakage 500	μΑ	$V_{DD} = 3.3 \text{ V}, V_{EN/BYPASS} = 0 \text{ V}.$
---------------------------------	-------------	----	--

#### **Thermal Data**

Thermal Resistance (Infrared Scan)	Θις	235	°C/W	On standard evaluation board (note 5).
Channel Temperature @ 85 °C reference (package base).	T <sub>CHANNEL</sub>	99	°C	V <sub>DD</sub> = 3.3 V, I <sub>DDQ</sub> = 18 mA. No RF applied. Dissipated Power = 59 mW ( <b>note 5</b> ).

**Note 3:** Switching Time: 50% of V<sub>EN/BYPASS</sub> to 90% of Pout. **Note 4:** Switching Time: 50% of V<sub>EN/BYPASS</sub> to 10% of Pout.

**Note 5:** MTTF >  $10^6$  hours for T<sub>CHANNEL</sub>  $\leq 170$  °C.



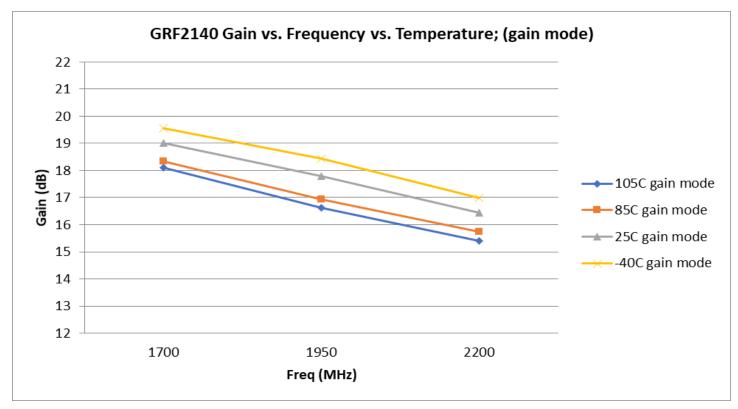


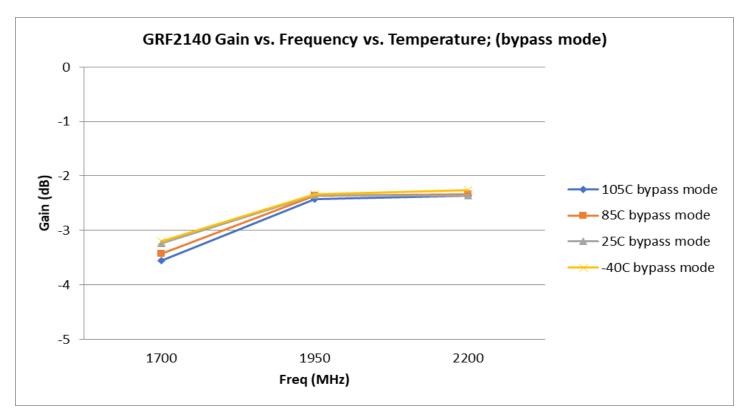
# **Nominal Operating Parameters - RF**

The following conditions apply unless noted otherwise: typical application schematic using the 1.7 to 2.2 GHz tuning set.  $V_{DD} = 3.3 \text{ V}$ ,  $V_{EN/BYPASS} = 3.3 \text{ V}$ ,  $I_{DDQ} = 18 \text{ mA}$ .  $M5 = 500 \Omega$ .  $F_{TEST} = 1.95 \text{ GHz}$ .  $T_{PKG BASE} = 25 ^{\circ}\text{C}$ . Evaluation board losses are included within the specifications.

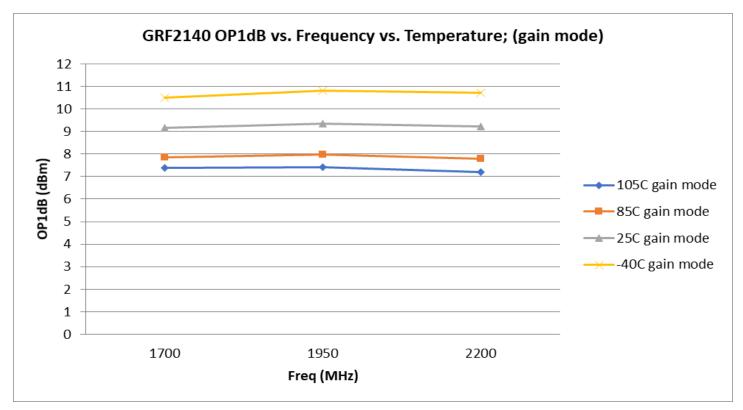
			Specification			
Parameter	Symbol	Min.	Min. Typ.		Unit	Condition
High Gain Mode						VDD = 3.3 V, VEN/BYPASS = 3.3 V.
Gain	S21	16.3	17.8		dB	
Output 3 <sup>rd</sup> Order Intercept Point	OIP3		20		dBm	2 MHz spacing (1949 and 1951 MHz).
Output 1 dB Compression Point	OP1dB	7.3	9.3		dBm	
Noise Figure	NF		1.1	1.3	dB	On standard evaluation board.
Bypass Mode						VDD = 3.3 V, VEN/BYPASS = 0 V.
Gain	S21	-3.5	-2.5		dB	
Output 3 <sup>rd</sup> Order Intercept Point	OIP3		39		dBm	2 MHz spacing (1949 and 1951 MHz).
Output 1 dB Compression Power	OP1dB		21.8		dBm	

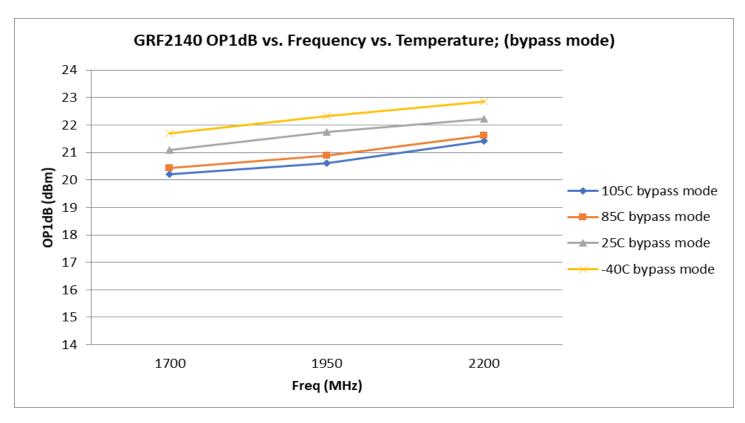




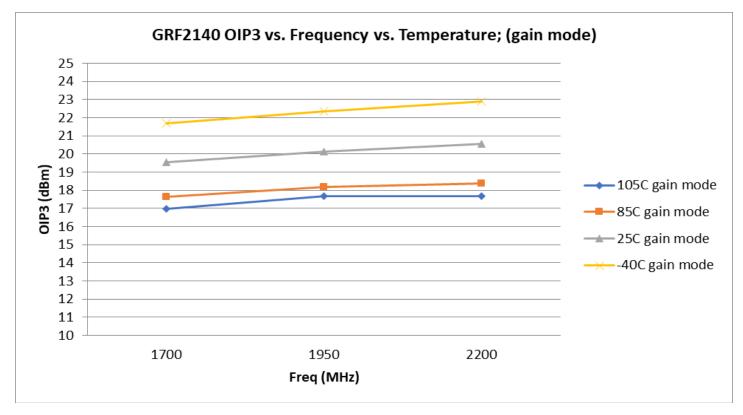


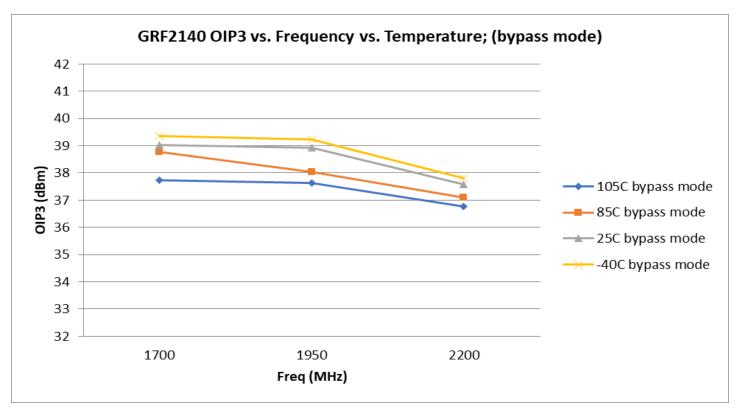




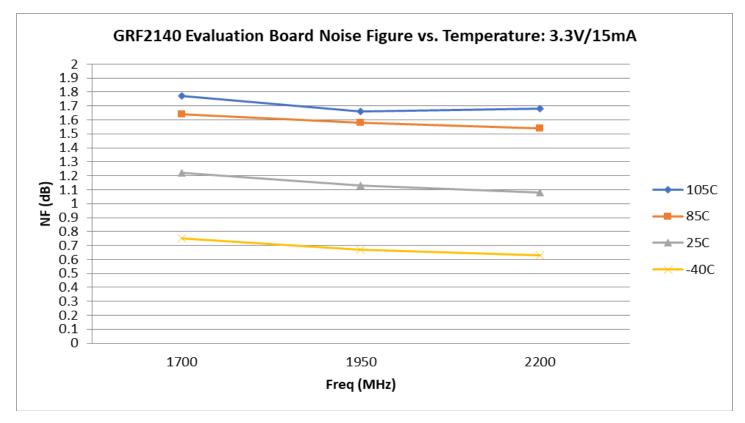












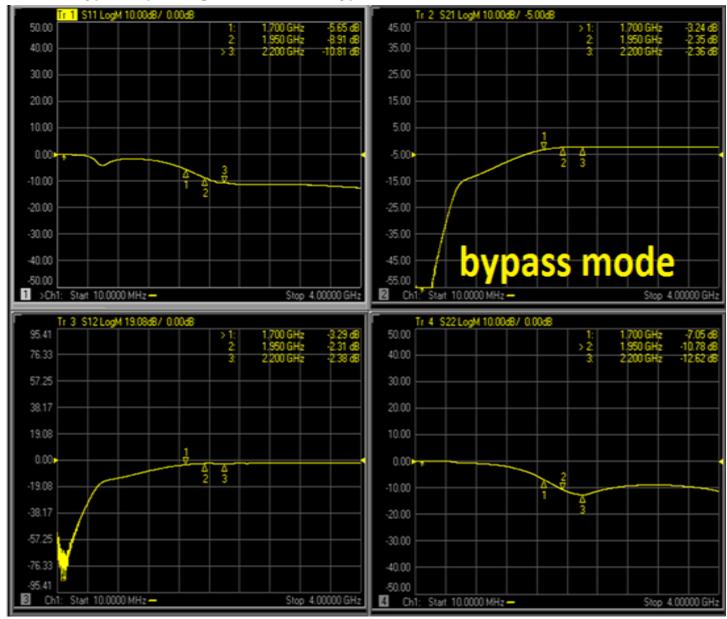


# **GRF2140 Typical Operating Curves: S-Pars: Gain Mode (1.7 to 2.2 GHz Tune)**



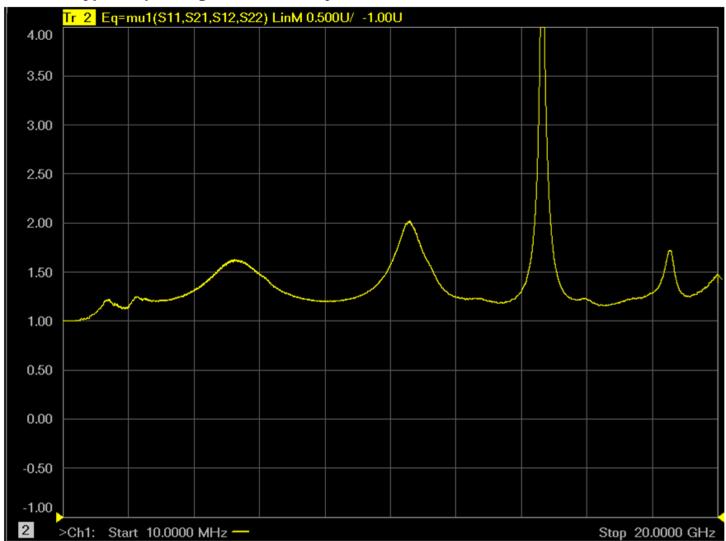


# **GRF2140 Typical Operating Curves: S-Pars: Bypass Mode (1.7 to 2.2 GHz Tune)**



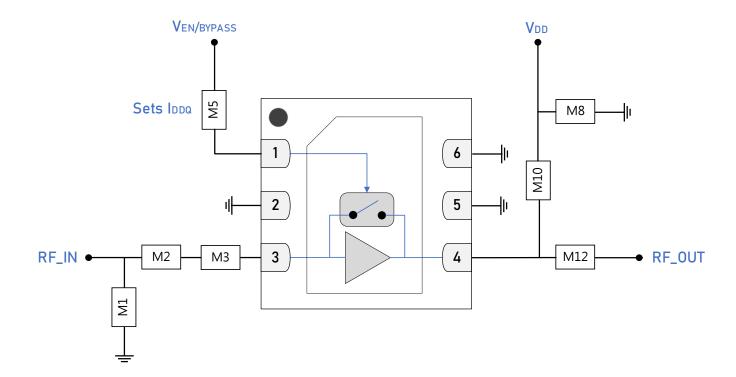


# **GRF2140 Typical Operating Curves: Stability Mu Factor (10 MHz to 20 GHz)**

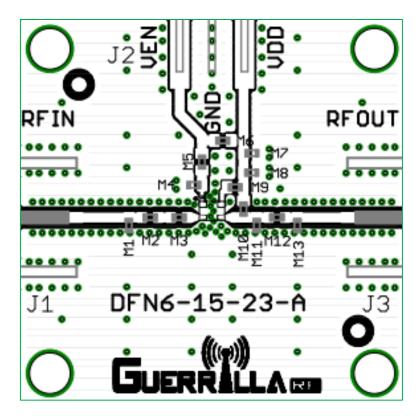


Note: Mu factor >= 1.0 implies unconditional stability.





**GRF2140 Standard Evaluation Board Schematic** 



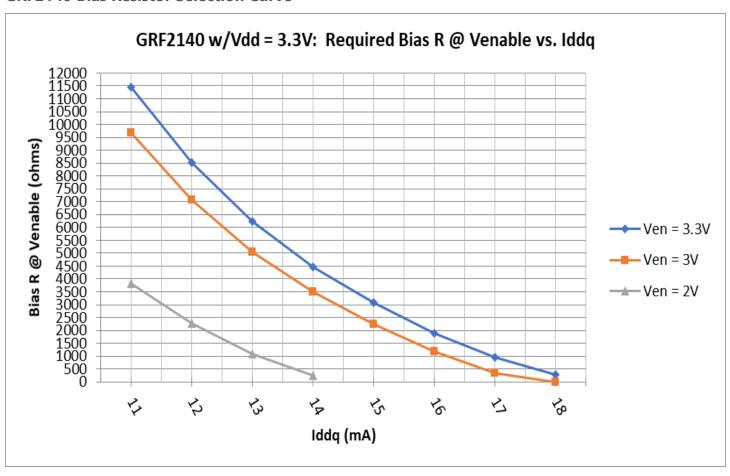
**GRF2140 Evaluation Board Assembly Diagram** 



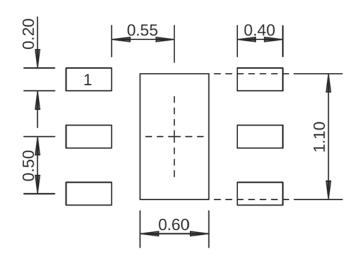
# **GRF2140 Evaluation Board Assembly Diagram Reference: 1.7 to 2.2 GHz Tune**

Component	Туре	Manufacturer	Family	Value	Package Size	Substitution
M1	Inductor	Murata	LQG	3.9 nH	0402	ok
M2	Capacitor	Murata	GJM	30 pF	0402	ok
M3	Inductor	Murata	LQG	1.5 nH	0402	ok
M5 (sets IDDQ)	Resistor	Various	5%	see curves	0402	ok
M8	Capacitor	Murata	GRM	0.1 μF	0402	ok
M10	Inductor	Murata	LQG	3.3 nH	0402	ok
M12	Capacitor	Murata	GRM	2.2 pF	0402	ok
Evaluation Board	DFN6-15-23-A					

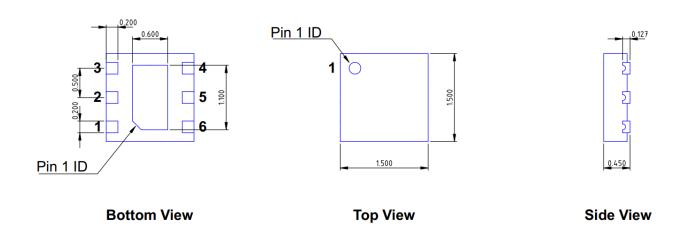
#### **GRF2140 Bias Resistor Selection Curve**







1.5 x 1.5 mm DFN-6 Suggested PCB Footprint (Top View)



DFN6 1.5x1.5mm

Dimensions in millimeters Dimensional Tolerance: ±0.05

# 1.5 x 1.5 mm DFN-6 Package Dimensions



# **Package Marking Diagram**



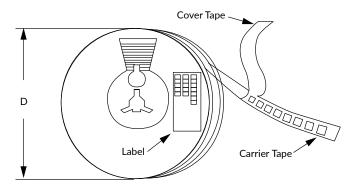
- Line 1: "Y" = YEAR (single digit). "WW" = WORK WEEK the Device was assembled.
- Line 2: "XXXX" = Device PART NUMBER.

#### **Tape and Reel Information**

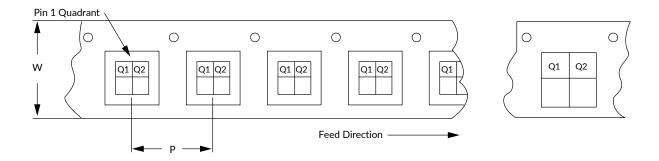
Guerrilla RF's tape and reel specification complies with Electronic Industries Alliance (EIA) standards for "Embossed Carrier Tape of Surface Mount Components for Automatic Handling" (reference EIA-481). See the following page for the Tape and Reel Specification and Device Package Information table, which includes units per reel.

Devices are loaded with pins down into the carrier pocket with protective cover tape and reeled onto a plastic reel. Each reel is packaged in a cardboard box. There are product labels on the reel, the protective ESD bag and the outside surface of the box.

For the Tape and Reel Reference Table, please refer to: Package Manufacturing Information | Guerrilla RF (guerrilla-rf.com)



Tape and Reel Packaging with Reel Diameter Noted (D)



Carrier Tape Width (W), Pitch (P), Feed Direction and Pin 1 Quadrant Information



# **GRF2140** Low Current LNA with Bypass 0.085 to 4.2 GHz

RELEASE A DATA SHEET

# **Revision History**

Revision Date	Description of Change
December 12, 2017	Preliminary Data Sheet.
October 24, 2019	Release Ø Data Sheet.
May 9, 2023	Release A Data Sheet. Upgraded Data Sheet to new format.
June 2, 2025	Extended frequency range from 100 - 3800 MHz to 85 - 4200 MHz.





#### GRF2140 Low Current LNA with Bypass 0.085 to 4.2 GHz

#### **RELEASE A DATA SHEET**

#### **Data Sheet Classifications**

Data Sheet Status	Notes
Advance	S-parameter and NF data based on EM simulations for the fully packaged device using foundry-supplied transistor S-parameters. Linearity estimates based on device size, bias condition and experience with related devices.
Preliminary	All data based on limited evaluation board measurements taken within the Guerrilla RF Applications Lab. All parametric values are subject to change pending the collection of additional data.
Release Ø	All data based on measurements taken with <i>production-released</i> material. TYP values are based on a combination of ATE and bench-level measurements, with MIN/MAX limits defined using <i>modelled estimates</i> that account for part-to-part variations and expected process spreads. Although unlikely, future refinements to the TYP/MIN/MAX values may be in order as multiple lots are processed through the factory.
Release A-Z	All data based on measurements taken with production-released material derived from multiple lots which have been fabricated over an extended period of time. MIN/MAX limits may be refined over previous releases as more statistically significant data is collected to account for process spreads.

Information in this Data Sheet is specific to the Guerrilla RF, Inc. ("Guerrilla RF") product identified.

This Data Sheet, including the information contained in it, is provided by Guerrilla RF as a service to its customers and may be used for informational purposes only by the customer. Guerrilla RF assumes no responsibility for errors or omissions on this data sheet or the information contained herein. Information provided is believed to be accurate and reliable, however, no responsibility is assumed by Guerrilla RF for its use, nor for any infringement of patents, or other rights of third parties, resulting from its use. Guerrilla RF assumes no liability for any data sheet, data sheet information, materials, products, product information, or other information provided hereunder, including the sale, distribution, reproduction or use of Guerrilla RF products, information, or materials.

No license, whether express, implied, by estoppel, by implication or otherwise is granted by this data sheet for any intellectual property of Guerrilla RF, or any third party, including without limitation, patents, patent rights, copyrights, trademarks, and trade secrets. All rights are reserved by Guerrilla RF.

All information herein, products, product information, data sheets, and data sheet information are subject to change and availability without notice. Guerrilla RF reserves the right to change component circuitry, recommended application circuitry and specifications at any time without prior notice. Guerrilla RF may further change its data sheet, product information, documentation, products, services, specifications, or product descriptions at any time, without notice. Guerrilla RF makes no commitment to update any materials or information and shall have no responsibility whatsoever for conflicts, incompatibilities, or other difficulties arising from any future changes.

GUERRILLA RF INFORMATION, PRODUCTS, PRODUCT INFORMATION, DATA SHEETS AND DATA SHEET INFORMATION ARE PROVIDED "AS IS" AND WITHOUT WARRANTY OF ANY KIND, WHETHER EXPRESS, IMPLIED, STATUTORY, OR OTHERWISE, INCLUDING FITNESS FOR A PARTICULAR PURPOSE OR USE, MERCHANTABILITY, PERFORMANCE, QUALITY OR NON-INFRINGEMENT OF ANY INTELLECTUAL PROPERTY RIGHT; ALL SUCH WARRANTIES ARE HEREBY EXPRESSLY DISCLAIMED. GUERRILLA RF DOES NOT WARRANT THE ACCURACY OR COMPLETENESS OF THE INFORMATION, TEXT, GRAPHICS OR OTHER ITEMS CONTAINED WITHIN THESE MATERIALS. GUERRILLA RF SHALL NOT BE LIABLE FOR ANY DAMAGES, INCLUDING BUT NOT LIMITED TO ANY SPECIAL, INDIRECT, INCIDENTAL, STATUTORY, OR CONSEQUENTIAL DAMAGES, INCLUDING WITHOUT LIMITATION, LOST REVENUES OR LOST PROFITS THAT MAY RESULT FROM THE USE OF THE MATERIALS OR INFORMATION, WHETHER OR NOT THE RECIPIENT OF MATERIALS HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGE.

Customers are solely responsible for their use of Guerrilla RF products in the Customer's products and applications or in ways which deviate from Guerrilla RF's published specifications, either intentionally or as a result of design defects, errors, or operation of products outside of published parameters or design specifications. Customers should include design and operating safeguards to minimize these and other risks. Guerrilla RF assumes no liability or responsibility for applications assistance, customer product design, or damage to any equipment resulting from the use of Guerrilla RF products outside of stated published specifications or parameters.